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provided on the same semiconductor substrate so that the light emitting active layers lie substantially in parallel to a main surface of the semiconductor substrate, and a high-resistance region provided between the semiconductor laser resonators.

16. (*Unamended*) A semiconductor laser device comprising:  
first and second semiconductor laser resonators provided on the same semiconductor substrate, an active layer of the first laser resonator being of a different material than an active layer of the second laser resonator;  
the active layer of the second laser resonator being provided in a groove, whereas the active layer of the first laser resonator is not provided in a groove; and  
a high-resistance region provided at least along a sidewall of the groove in which the active layer of the second laser resonator is provided, the high-resistance region comprising ions and/or protons implanted into the sidewall of the groove.

#### REMARKS

This is in response to the Office Action dated September 25, 2002. Claims 1-11, 16 and 17 are pending. Attached hereto is a marked-up version of the changes made to the claim(s) by the current amendment. The attached page(s) is captioned "Version With Markings To Show Changes Made."

For purposes of example and without limitation, certain example embodiments of this invention relate to a semiconductor laser device including multiple laser resonators. One laser resonator may emit light at a *first wavelength*, and another resonator may emit